

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

1. - 21. (Cancelled)

22. (Currently Amended) A capacitor of a semiconductor device, the capacitor comprising:

a lower electrode;

an AHO((Al<sub>x</sub>Hf<sub>1-x</sub>)O<sub>y</sub>) film formed on the lower electrode;

an upper electrode formed on the AHO film; and

a dielectric film having a dielectric constant that is higher than that of the AHO film between the upper electrode and the AHO layer,

wherein the dielectric film is an HfO<sub>2</sub> layer, a ZrO<sub>2</sub> layer, or an STO layer, and

wherein the dielectric film is directly in contact with the upper electrode.

23. (Original) The capacitor of claim 22, further comprising an oxidation barrier film formed between the lower electrode and the AHO layer.

24. - 37. (Cancelled)